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PTO/SB/08A (08-00)

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INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT

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Sheet

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of

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## Complete if Known

Application Number	(filed herewith)
Filing Date	August 6, 2001
First Named Inventor	Becker et al.
Group Art Unit	
Examiner Name	
Attorney Docket Number	11762.0284.CNUS01

## U.S. PATENT DOCUMENTS

Examiner Initials	Cite No. <sup>1</sup>	U.S. Patent Document Number	Kind Code <sup>2</sup> (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
George	A1	4,734,157		Carbaugh et al.	03-29-1988	
	A2	4,789,680		Yan	12-06-1988	
	A3	4,877,841		Dory	10-31-1989	
	A4	4,824,811		Vogel et al.	04-13-1982	
	A5	4,912,061		Negr	03-27-1990	
	A6	4,588,410		Thomquist	02-04-1988	
	A7	3,479,237		Bergh et al.	11-18-1989	
	A8	4,871,655		Stefano et al.	11-20-1988	
	A9	5,013,392		Long et al.	05-07-1991	
	A10	5,040,046		Chhebana et al.	08-13-1991	
	A11	4,244,752		Henderson et al.	01-13-1981	
	A12	4,374,898		Sanders et al.	02-22-1983	
	A13	4,581,101		Senoue et al.	04-08-1988	
	A14	5,043,790		Butler	08-27-1991	
	A15	5,013,692		Ide et al.	05-7-1991	
	A16	4,878,420		Bach	12-18-1988	
	A17	4,180,432		Clark	12-25-1979	
	A18	4,734,152		Gels et al.	03-28-1988	
	A19	5,021,121		Grochel et al.	08-04-1991	
George	A20	4,439,270		Powell et al.	03-27-1984	

## FOREIGN PATENT DOCUMENTS

Examiner Initials	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sub>6</sub>
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				
	B1	JP	59-53833		Okano	03-30-1988		
	B2	JP	1-15930		Omoto	01-18-1989		
	B3	JP	2-62038		Kadomura	03-01-1990		
	B4	JP	4-298032		Nobeshima	10-21-1992		
	B5	JP	4-180222		Mashiro	08-28-1992		
	B6	EP	651434		Yank et al.	05-03-1985		

Examiner  
Signature

George Goudrean

Date  
Considered

9-03

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<sup>1</sup> Unique citation designation number. <sup>2</sup> See attached Kinds of U.S. Patent Documents. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

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## **INFORMATION DISCLOSURE STATEMENT BY APPLICANT**

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Sheet 2 of 5

Complete If Known	
Application Number	(filed herewith)
Filing Date	August 6, 2001
First Named Inventor	Becker et al.
Group Art Unit	3632
Examiner Name	AB
Attorney Docket Number	11762.0284.CN1US01

**U.S. PATENT DOCUMENTS**

U.S. PATENT DOCUMENTS					
Examiner Initials *	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code <sup>2</sup> (if known)		
GJW	A21	5,376,233		Man	12-27-1994
	A22	5,338,398		Szwejkowski et al.	08-18-1994
	A23	5,316,618		Nakamura et al.	05-31-1994
	A24	5,470,788		Yanai et al.	11-28-1995
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	A27	5,423,945		Marks et al.	06-13-1995
	A28	5,242,538		Hannak et al.	09-07-1993
	A29	5,491,280		Galleider	09-19-1995
	A30	5,558,501		Collins et al.	09-17-1998
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	A32	5,286,344		Blalock et al.	02-16-1994
	A33	5,093,277		Arima et al.	03-03-1992
	A34	4,241,185		Hughes et al.	12-23-1980
	A35	4,438,270		Powell et al.	03-27-1984
	A36	5,286,667		Lin et al.	02-16-1994
GJW	A37	5,364,804		Ho et al.	11-15-1994
	A38				
	A39				
	A40				

## FOREIGN PATENT DOCUMENTS

**Examiner  
Signature**

George Gould year

Date  
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9-031

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<sup>1</sup> Unique citation designation number. <sup>2</sup> See attached *Kinds of U.S. Patent Documents*. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 18 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

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INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT

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Sheet 3 of 5

## Complete if Known

Application Number	(filed herewith)
Filing Date	August 6, 2001
First Named Inventor	Becker et al.
Group Art Unit	
Examiner Name	

Attorney Docket Number 11762.0284.CNUS01

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## OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
	C1	"Crown-Shaped Capacitor Cell for 1.5V, Operation 65 Mb DRAMS" (Toshi Kage, et al.) IEEE Transactions on Electron Devices, vol. 38, No. 2, 1991.	
	C2	"VLSI Device Fabrication Using Unique, Highly-selective Si3N4 Dry Etching" (T. Kur et al.) Proceeding of the International Electron Devices Meeting (IEDM), 1983, pp. 757-760.	
	C3	"Formation of Contacts in a Planarized SiO2/Si3N4/SiO2 Dielectric Structure" (Paul E. Riley, Konrad K. Youn, and Charles C. Liu) J. Electrochem Soc, vol. 139, No 8 Sep. 1992.	
	C4	A method of obtaining a high oxide to nitride selectivity in an MERIE Reactor, by David S. Becker, Guy Blalock, 1993 Symposium of Dielectric Science and Technology and Electronics Divisions of The Electrochemical Society, vol. 93-21, pp. 178-189 (May 19, 1993).	
	C5	"Selective Oxide: Nitride Dry Etching in a High Density Plasma Reactor" by M. Armacost, J. Marks, 1993 Symposium of Dielectric Science and Technology and Electronics Divisions of The Electrochemical Society, vol. 93-21, pp. 190-200 (May 19, 1993).	
	C6	"Self-Aligned Bitline Contact for 4 Mbit DRAM" K.H. Kuesters, H.M. Muethoff, G. Enders, E.G. Mohr, W. Mueller, pp. 640-649, 1987.	
	C7	"A Buried-Plate Trench Cell for a 64-Mb DRAM", Kenney et al., 1992 Symposium of VLSI, IEEE.	
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	C9	"High-Rate and Highly Selective Etching of SiO2 Using Microwave Plasma", M. Nawata, Y. Kakehi, S. Kanai, Y. Kawasaki, K. Tsuchikuni, and H. Enami, 1993 Meeting Electrochemical Society, Honolulu, Hawaii, pp. 229-234 (1993).	
	C10	"Influence of Resist Transport on Fluorine RIE of Deep Trenches in Si", J.C. Arnold, D.C. Gray and H. H. Swain, J. Vac. Sci. Technol. B vol. 11, No. 8, pp. 2071-2080 (Nov. 1993).	
	C11	"Influence of Different Etching Mechanisms on the Angular Dependence of Si3N4 Etching", A.M. Barklund and H.O. Blom, J. Vac. Sci. Technol. A vol. 11, No. 4, pp. 1226-1229, (Jul. 1993).	

Examiner Signature	Date Considered

<sup>1</sup> EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT

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Sheet 4 or 5

## Complete If Known

Application Number	(filed herewith)
Filing Date	August 6, 2001
First Named Inventor	Becker et al.
Group Art Unit	5200
Examiner Name	
Attorney Docket Number	11762.0284.CNUS01

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## OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
	C12	"Mass Spectrometric Studies of Plasma Etching of Si3N4", P.E. Clarke, D. Field, A.J. Hydes, D.F. Kiemperer and M.J. Seakins, J. Vac. Sci. Technol. B vol. 3, No. 6, pp. 1614-1618, Nov. 1985.	
	C13	"Microtrench Formation in Polysilicon Plasma Etching Over Thin Gate Oxide", T.J. Dalton, J.C. Arnold, M.H. Sawni, S. Swan, and D. Cortes, J. Electrochem. Soc., vol. 140, No. 8, pp. 2355-2401 (Aug. 1993).	
	C14	"Radical Kinetics in a Fluorocarbon Etching Plasma", Y. Hikosaka and H. Sugai, Jpn. Appl. Phys., vol. 32, No. 8, pp. 3040-3044 (Jun. 1993).	
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	C18	"Suppression of Microloading Effect by Low-Temperature SiO2 Etching", M. Sato, D. Takerhara, K. Uda, K. Sakiyama and T. Hara, Jpn. J. Appl. Phys., vol. 31, No. 12B, pp. 4370-4375 (Dec. 1992).	
	C19	"Novel Surface Reaction Model in Dry-Etching A. Misaka, K. Harataji, M. Kubota and N. Nomura, Process Simulator", Jpn. J. Appl. Phys., vol. 31, Pt. 1, No. 12B, pp. 4363-4369. (Dec. 1992).	
	C20	"Silicon Etching Mechanisms in a CF4/H2 Glow Discharge", G.S. Oehrlein and H.L. Williams, J. Appl. Phys., vol. 62, No. 2, pp. 862-872 (Jul. 1987).	
	C21	"SiO2 Tapered Etching Employing Magnetron Discharge of Fluorocarbon Gas", T. Ohwra, K. Honoka, T. Artieda, I. Hasegawa and H. Okano, Jpn. J. Appl. Phys., vol. 31, Pt. 1, No. 2A, pp. 405-410 (1992).	
	C22	"Gas Mixing to Prevent Polymer Formation During Reactive Ion Etching", Bondur et al., IBM Tech. Disclosure Bulletin, vol. 21, No. 10, Mar. 1978, pp. 4016.	

Examiner Signature		Date Considered	

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INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT

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Sheet 5 of 5

## Complete if Known

Application Number	(filed herewith)
Filing Date	August 6, 2001
First Named Inventor	Becker et al.
Group Art Unit	164
Examiner Name	
Attorney Docket Number	11762.0284.CNUS01

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS		
Examiner Initials *	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
	C23	'Plasma Cleaning by Use of Hollow-Cathode Discharge in A Trifluoromethane-Silicon Dioxide Dry Etching System', Watanabe, Feb. 1992, Japanese Journal of Applied Physics, Part 1, 31 (5A), pp. 1491-1498.
	C24	Loewenstein, 'Temperature Dependence of Silicon Nitride Etching by Atomic Fluorine', American Institute of Physics, 1989, vol. 65, No. 1, pp. 386-387.
	C25	Loewenstein, 'Selective Etching of Silicon Nitride Using Remote Plasmas of CF <sub>3</sub> and SF <sub>6</sub> ', American Vacuum Society, 1989, vol. 7, No. 3, pp. 686-690.
	C26	Yasuo Nagahiro, 'Self Aligned Contact Development Activity Increases Aligned for Large Scale Manufacturing Around 0.25 MM Era Problem of Etching Technology: Improvement of Si3N <sub>4</sub> Selectivity Ratio', Nikkei Microdevices, Feb. 1995, pp. 54-61.
	C27	'Gas Mixing to Prevent Polymer Formation During Reactive Ion Etching', J.A. Bondur and C.F. Crimi, IBM Technical Disclosure Bulletin, vol. 21 No. 10, Mar. 1979.
	C28	'Developments in Plasma Processing', R.A. Gottscho, AT&T Bell Labs, 1994 American Vacuum Society Symposium, p. 120.
	C29	'Self-Aligned Contact (SAC) Dry Etch Process for 0.5u SRAM Technology', J.E. Nulty, P.S. Trammell, Cypress Semiconductor, 1994 American Vacuum Society Symposium, p. 120.
	C30	
	C31	
	C32	
	C33	

Examiner Signature		Date Considered	
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Form PTO-1449 (modified)		Atty. Docket No. 11762.0284.CNUS01	Serial No. 09/923,058
List of Patents and Publications for Applicant's INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		Applicant Becker, et. al.	
		Filing Date: August 06, 2001	Group: 1763
U.S. Patent Documents <i>See Pages 1-2</i>	Foreign Patent Documents <i>See Page 2</i>	Other Art <i>See Pages 3-4</i>	

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 GROUP 1763

### U.S. Patent Documents

Exam. Init.	Ref. Des.	Document Number	Date	Name	Class	Sub Class	Filing Date of App.
GRG	A1	5,772,832	06/30/98	Collins, et al.	156	345	04/04/97
GRG	A2	5,888,414	03/30/99	Collins, et al.	216	68	09/24/97
	A3	6,194,325	02/27/01	Yang, et al.	438	740	12/04/95
	A4	5,880,037	03/09/99	Arleo, P.	438	740	10/09/97
	A5	5,477,975	12/26/95	Rice, et al.	216	68	10/15/93
	A6	5,556,501	09/17/96	Collins, et al.	156	345	04/04/93
	A7	6,184,150	02/06/01	Yang, et al.	438	740	10/27/97
	A8	5,562,801	10/08/96	Nulty, J.E.	156	643.1	12/07/94
	A9	4,350,578	09/21/82	Frieser, et al.	204	192 R	05/11/81
	A10	4,368,092	01/11/83	Steinberg, et al.	156	345	08/05/81
	A11	4,377,438	03/22/83	Moriya, et al.	156	643	09/22/81
	A12	4,401,054	08/30/83	Matsuo, et al.	118	723	04/27/81
	A13	4,492,620	01/08/85	Matsuo, et al.	204	192 R	09/09/83
	A14	4,511,430	04/16/85	Chen, et al.	156	643	01/30/84
	A15	4,675,073	06/23/87	Douglas, M.	156	643	03/07/86
	A16	4,711,698	12/08/87	Douglas, M.	156	643	07/15/85
	A17	4,778,561	10/18/88	Ghanbari, E.	156	643	10/30/87
	A18	4,807,016	02/21/89	Douglas, M.	357	67	11/20/87
	A19	4,918,031	04/17/90	Flamm, et al.	437	225	12/28/88
	A20	4,948,458	08/14/90	Ogle, J.S.	156	643	08/14/89
	A21	5,091,326	02/25/92	Haskell, J.D.	437	43	09/12/90
	A22	5,269,879	12/14/93	Rhoades, et al.	156	643	10/16/91
GRG	A23	5,296,095	03/22/94	Nabeshima, et al.	156	662	10/30/91

EXAMINER: George Goldstein DATE CONSIDERED: 9-03

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INFORMATION DISCLOSURE STATEMENT — PTO-1449 (MODIFIED)

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Form PTO-1449 (modified)

List of Patents and Publications for Applicant's

## INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

Atty. Docket No.  
11762.0284.CNUS01Serial No.  
09/923,058Applicant  
Becker, et. al.Filing Date:  
August 06, 2001Group:  
1763

U.S. Patent Documents

See Pages 1-2

Foreign Patent Documents

See Page 2

Other Art  
See Pages 3-4

## U.S. Patent Documents

Exam. Init.	Ref. Des.	Document Number	Date	Name	Class	Sub Class	Filing Date of App.
gpa	A24	5,429,710	07/04/95	Akiba, et al.	216	17	02/16/94
gpa	A25	5,468,342	11/21/95	Nulty, et al.	156	643.1	04/28/94
gpa	A26	5,503,901	04/02/96	Sakai, et al.	428	161	06/29/94
gpa	A27	5,880,036	03/09/99	Becker, et al.	438	740	11/15/93
	A28						
	A29						

## Foreign Patent Documents

Exam. Init.	Ref. Des.	Document Number	Date	Country	Class	Sub Class	Translation Yes/No
	B1	0520519 A1	12/30/92	EPO			Yes
	B2	55009464	01/23/80	Japan	H01L	27/08	Abstract Only
	B3	0 050 972 A2	05/05/82	EPO	H01L	21/88	Yes
	B4	57210631	12/24/82	Japan	H01L	21/302	Abstract Only
	B5	60111474	06/17/85	Japan	H01L	29/80	Abstract Only
	B6	61-224423	10/06/86	Japan	H01L	21/302	Abstract Only
	B7	0 265 584 A2	04/05/88	EPO	H01L	21/31	Yes
	B8	2 175 542 A	12/03/86	United Kingdom	C23F	1/02	Yes
	B9	2062038	03/01/90	Japan	H01L	21/302	Abstract Only
	B10	0 552 490 A1	07/28/93	EPO	H01L	21/311	Yes
	B11	0 644 584 A1	03/22/95	EPO	H01L	21/311	Yes
	B12						

EXAMINER: George Goudreau

DATE CONSIDERED: 9-031

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INFORMATION DISCLOSURE STATEMENT — PTO-1449 (MODIFIED)

Form PTO-1449 (modified)		Atty. Docket No. 11762.0284.CNUS01	Serial No. 09/923,058
List of Patents and Publications for Applicant's INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		Applicant Becker, et. al.	
		Filing Date: August 06, 2001	Group: 1763
U.S. Patent Documents See Pages 1-2	Foreign Patent Documents See Page 2	Other Art See Pages 3-4	
<b>Other Art (Including Author, Title, Date Pertinent Pages, Etc.)</b>			
Exam. Init.	Ref. Des.	Citation	
	C1	Watanabe, S., "Plasma Cleaning by Use of Hollow-Cathode Discharge in a CHF <sub>3</sub> -SiO <sub>2</sub> Dry-Etching System", <i>Japanese J. Appl. Physics</i> 1992, 31; 1491-1498.	
	C2	Yasuaki Nagahiro, "Self-Aligned Contact Development Activity Increases Aimed for Large Scale Manufacturing Around 0.25 Mm Era Problem of Etching Technology: Improvement of Si <sub>3</sub> N <sub>4</sub> Selectivity Ratio", <i>Nikkei Microdevices</i> , Feb. 1995, pp. 54-61.	
	C3	Gottsch, R.A., "Recent Developments in Plasma Processing", AT&T Bell Laboratories, 1994, <i>American Vacuum Society Symposium</i> , p. 120.	
	C4	Nulty, J.E.; Trammel, P.S., "Self-Aligned Contact (SAC) Dry Etch Process of 0.5m SRAM Technology", <i>1994 American Vacuum Society Symposium</i> , p. 120.	
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	C6	"High Rate and Highly Selective SiO <sub>2</sub> Etching Employing Inductively Coupled Plasma", Y. Honike; K. Kubota; T. Fukazawa, Tokyo University, <i>1994 American Vacuum Society Symposium</i> , p. 120.	
	C7	Yin, G.Z.; Ben-Dor, M.; Chang, M.S.; Yep, T.O. "High-Selectivity Plasma Etching of Silicon Dioxide on Single-Wafer Etchers", <i>Journal of Vacuum Science &amp; Technology A</i> 1989, A7(3); 691-695.	
	C8	Bariya, A.J.; Shan, H.; Frank, C.W.; Self, S.A.; McVittie, J.P., "The Etching of CHF <sub>3</sub> Plasma Polymer in Fluorine-Containing Discharges", <i>Journal of Vacuum Science and Technology B</i> 1991, 9 (1); 1-7.	
	C9	Machida, K.; Oikawa, H., "SiO <sub>2</sub> Planarization Technology with Biasing and Electron Cyclotron Resonance Plasma Deposition for Submicron Interconnections", <i>Journal of Vacuum Science and Technology B</i> 1986, 4; 818-821.	
	C10	Anonymous, "Selective Reactive Ion Etch for Silicon Oxide Over Silicon Nitride", <i>Research Disclosure</i> 1989, 301; 340.	
	C11	Moss, S.J., et al. Eds. "Plasma Etching", in <i>The Chemistry of the Semiconductor Industry</i> , New York: Blackie & Son Ltd., 1987, pp. 374-378.	
	C12	D'Agostino, R., "Summary Abstract: Mechanisms of Polymerization in Discharges of Fluorocarbons", <i>Journal of Vacuum Science and Technology A</i> 1985, 3 (6); 2627-2628.	

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Form PTO-1449 (modified)		Atty. Docket No. 11762.0284.CNUS01	Serial No. 09/923,058
List of Patents and Publications for Applicant's INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		Applicant Becker, et. al.	Filing Date: August 06, 2001
		Group: 1763	
U.S. Patent Documents See Pages 1-2	Foreign Patent Documents See Page 2	Other Art See Pages 3-4	

Other Art (Including Author, Title, Date Pertinent Pages, Etc.)		
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	C13	Riley, P.E.; Hanson, D.A., "Comparison of Etch Rates of Silicon Nitride, Silicon Dioxide, and Polycrystalline Silicon Upon O <sub>2</sub> Dilution of CF <sub>4</sub> Plasmas", <i>Journal of Vacuum Science and Technology B</i> 1989, 7(6); 1352-1356.
	C14	Oehrlein, G.S.; Lee, Y.H., "Reactive Ion Etching Related Si Surface Residues and Subsurface Damage: Their Relationship to Fundamental Etching Mechanisms", <i>Journal of Vacuum Science and Technology A</i> 1987, 5 (4); 1585-1594.
	C15	Gilboa, H.; Hata, W.; O'Donnell, K., "Nondestructive Characterization of RIE Induced Radiation Damage Using Surface Acoustic Waves", <i>Mat. Res. Soc. Symp. Proc.</i> 1985, 38 511-517.
	C16	Truesdale, B.A.; Smolinsky, G.; Mayer, T.M., "The Effect of Added Acetylene on the RF Discharge Chemistry of C <sub>2</sub> F <sub>6</sub> , A Mechanistic Model for Fluorocarbon Plasmas", <i>J. Applied Physics</i> 1980, 51(5); 2909-2913.
	C17	Norström, H.; Buchta, R.; Ranovc, F.; Wiklund, P., "RIE of SiO <sub>2</sub> in Doped and Undoped Fluorocarbon Plasmas", <i>Vacuum</i> 1982, 32 (12); 737-745.
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List of Patents and Publications for Applicant's		Applicants:	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		David S. Becker, et al.	
		Filing Date:	Group:
		August 6, 2001	1763
U.S. Patent Documents See Page 1		Foreign Patent Documents See Page 1	Other Art See Page 1

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## U.S. Patent Documents

Exam. Init.	Ref. Des.	Document Number	Date	Name	Class	Sub Class	Filing Date of App.
	A1						

## Foreign Patent Documents

Exam. Init.	Ref. Des.	Document Number	Date	Country	Class	Sub Class	Translation Yes/No
	B1						

## Other Art (Including Author, Title, Date Pertinent Pages, Etc.)

Exam. Init.	Ref. Des.	Citation
<i>gag</i>	C1	Complaint for Declaratory Relief, filed in <i>Sandisk Corp. v. Micron Tech., Inc.</i> , Case. No. C-02-2627VRW (N. D. Cal.).
	C2	

EXAMINER: George Gouldman DATE CONSIDERED: 9-63

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